



Bipolar PNP Bare Die – BTP131

Part Description

The BTP131 is a silicon BJT transistor available in bare die form and well suited for use in High Voltage Driver applications. NPN complement is BTN131.

Key Parameters:

- VCBO = -300V
- VCEO = -300V
- VEBO = -7V
- hFE = 60-280 @ VCE = -10V, IC = -0.01A
- VCE(Sat) = -0.5V @ IC = -0.1A, IB = -10mA
- fT = 65 MHz @ VCE = -10V, IE = 0A
- COBO = 4pF @ VCB = -20V

Features

Designed to provide performance equivalent to MPSA92

Die Size (Unawn)

660µm X 660µm, 26 Mils X 26 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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